Schottky Barrier Diode

FF1J4L

● **Features**

- Super small size
- Various kinds
- Taping capable of high density mounting

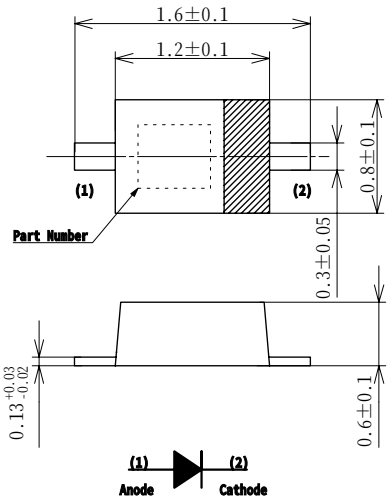
● **Applications**

- Small size power supplies
- OR diode : Preventing from reverse current by wrong setting of a battery .

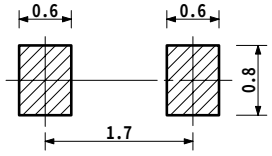
● **Structures**

- Resin molded, and Silicon Schottky Barrier Diode.
- Marking symbol : [C]
- Terminal plating : Sn-2Bi
- Conforms to RoHS regulations

● **Outline Drawing** Unit : mm



● **Recommendation Pattern for Mounting**



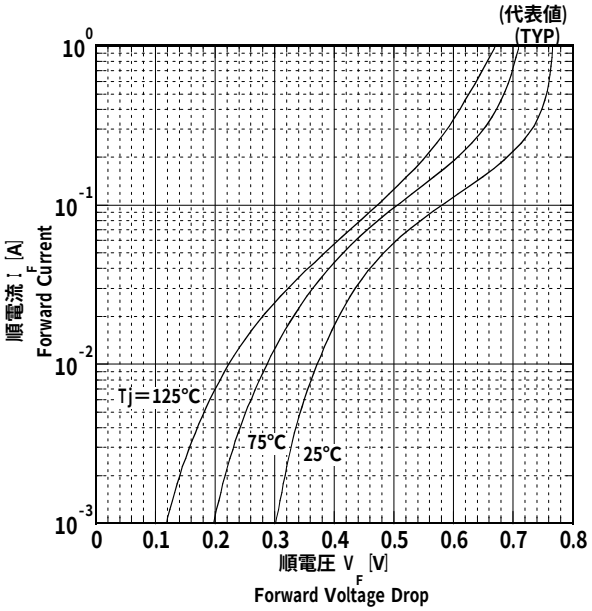
● **Absolute Maximum Ratings**

Items	Symbol	Conditions	Ratings	Unit
Repetitive Peak Reverse Voltage	V_{RM}		40	V
Non-Repetitive Peak Reverse Voltage	V_{RSM}		45	V
Average Rectified Forward Current	I_O	Ta=25°C, Half sin wave 180 ° ,Resistive Load	100	mA
Peak Forward Surge Current	I_{FSM}	Tj=25°C, 50Hz, Single-phase, Half sin wave, Non-Repetitive	1	A
Operating Junction Temperature	T_j		-40～+125	°C
Storage Temperature	T_{stg}		-55～+125	°C

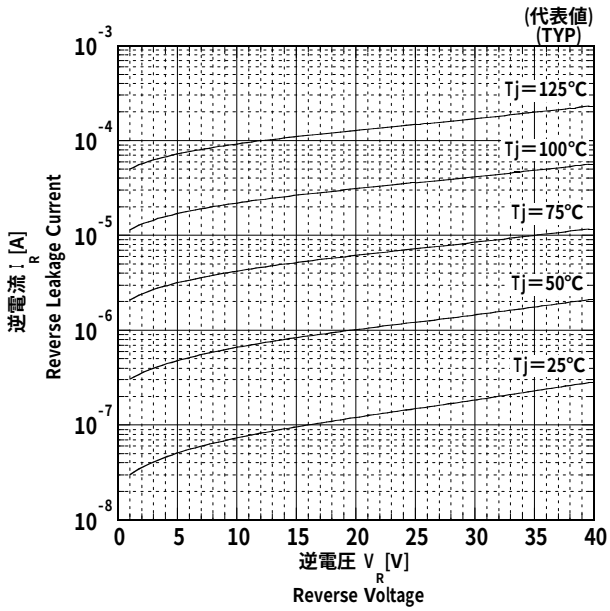
● **Electrical Characteristics (Tj=25°C)**

Items	Symbol	Conditions	TYP.	MAX.	Unit
Forward Voltage Drop	V_{F1}	I_F=0.1μA	280	-	mV
	V_{F2}	I_F=1mA	350	-	mV
	V_{F3}	I_F=100mA	510	600	mV
Reverse Leakage Current	I_{R1}	V_R=10V	0.09	-	μA
	I_{R2}	V_R=40V	-	5.0	μA
Junction Capacitance	Cj	V_R=10V,f=1MHz	8.0	-	pF
Thermal resistance	Rth(j-a)	Glass Epoxy Substrate, PC board : □20mm, Cu land : □4mm	-	400	°C/W

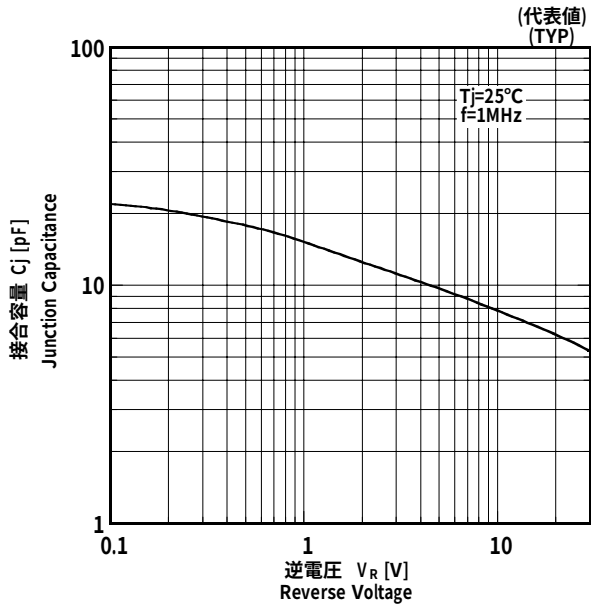
● Characteristics Diagrams



FORWARD CHARACTERISTICS



REVERSE CHARACTERISTICS



TYPICAL JUNCTION CAPACITANCE